TOSHIBA Transistor Silicon PNP Triple Diffused (PCT process)

# 2SA1255

### **High Voltage Switching Applications**

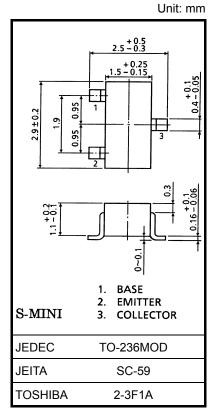
• High voltage:  $V_{CBO} = -200 \text{ V (min)}$   $V_{CEO} = -200 \text{ V (min)}$ 

- Small package
- Complementary to 2SC3138

### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V <sub>CBO</sub>	-200	V	
Collector-emitter voltage	V <sub>CEO</sub>	-200	V	
Emitter-base voltage	V <sub>EBO</sub>	-5	V	
Collector current	IC	-50	mA	
Base current	ΙΒ	-20	mA	
Collector power dissipation	PC	150	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T <sub>stg</sub>	-55~125	°C	

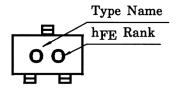
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



Weight: 0.012 g (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Marking



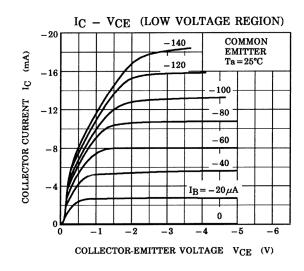


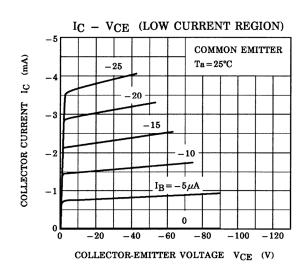
# **Electrical Characteristics (Ta = 25°C)**

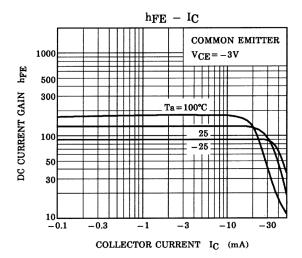
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	current	I <sub>CBO</sub>	$V_{CB} = -200 \text{ V}, I_E = 0$	_	_	-0.1	μА
Emitter cut-off cu	rrent	I <sub>EBO</sub>	$V_{EB} = -5 \text{ V}, I_{C} = 0$	_	_	-0.1	μА
Collector-base br	eakdown voltage	V (BR) CBO	$I_C = -0.1 \text{ mA}, I_E = 0$	-200	_	_	V
Collector-emitter	breakdown voltage	V (BR) CEO	$I_C = -1 \text{ mA}, I_B = 0$	-200	_	_	V
DC current gain		h <sub>FE</sub> (Note)	V <sub>CE</sub> = -3 V, I <sub>C</sub> = -10 mA	70	_	240	
Collector-emitter	saturation voltage	V <sub>CE</sub> (sat)	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$	_	-0.2	-1	V
Base-emitter satu	ıration voltage	V <sub>BE</sub> (sat)	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$	_	-0.75	-1.5	V
Transition freque	ncy	f <sub>T</sub>	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$	50	100	_	MHz
Collector output of	capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	3	7	pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{CC} = -50 \text{ V}, I_C = -6 \text{ mA}$ $-I_{B1} = I_{B2} = 0.6 \text{ mA}$ Pulse width = 5 $\mu$ s Duty cycle $\leq 2\%$	_	0.3		
	Storage time	t <sub>stg</sub>			2	_	μS
	Fall time	t <sub>f</sub>		_	0.4		

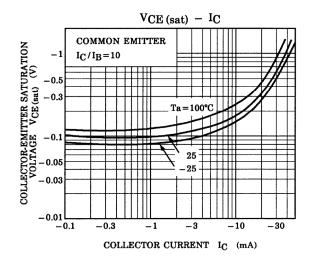
Note:  $h_{FE}$  classification O: 70~140, Y: 120~240

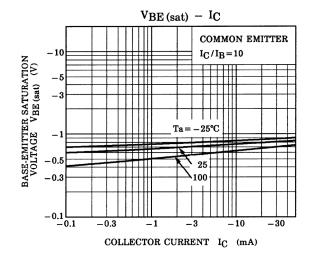
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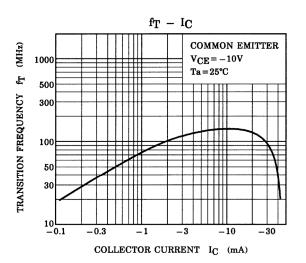


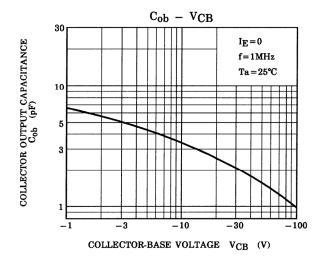


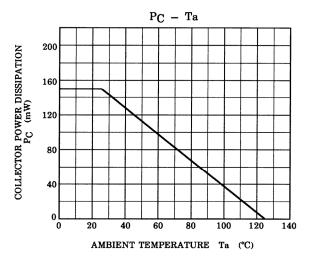












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20070701-EN GENERAL

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